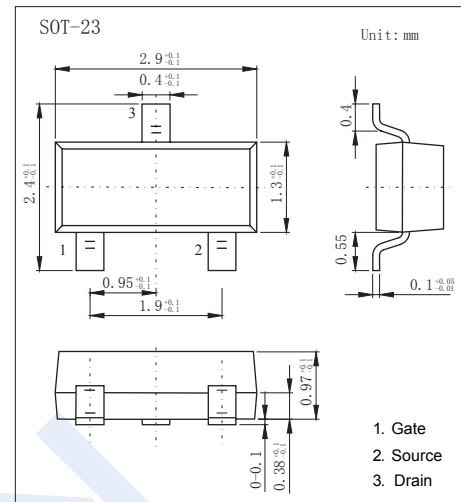
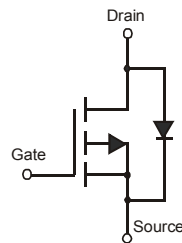


P-Channel MOSFET

DMP1260 (KMP1260)

■ Features

- $V_{DS} (V) = -20V$
- $I_D = -3.3 A$
- $R_{DS(ON)} < 75m\Omega$ ($V_{GS} = -4.5V$)
- $R_{DS(ON)} < 140m\Omega$ ($V_{GS} = -2.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	-20	V	
Gate-Source Voltage	V_{GS}	± 12		
Continuous Drain Current	I_D	$T_a = 25^\circ C$	-3.3	A
		$T_a = 70^\circ C$	-2.6	
Pulsed Drain Current	I_{DM}	-13		
Power Dissipation	P_D	1.4	W	
Thermal Resistance Junction- to-Ambient	R_{thJA}	90	$^\circ C/W$	
Junction Temperature	T_J	150	$^\circ C$	
Junction Storage Temperature Range	T_{stg}	-55 to 150		

P-Channel MOSFET

DMP1260 (KMP1260)

■ Electrical Characteristics Ta = 25°C

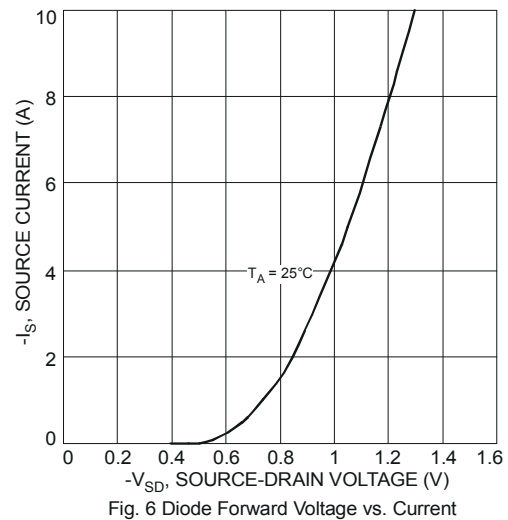
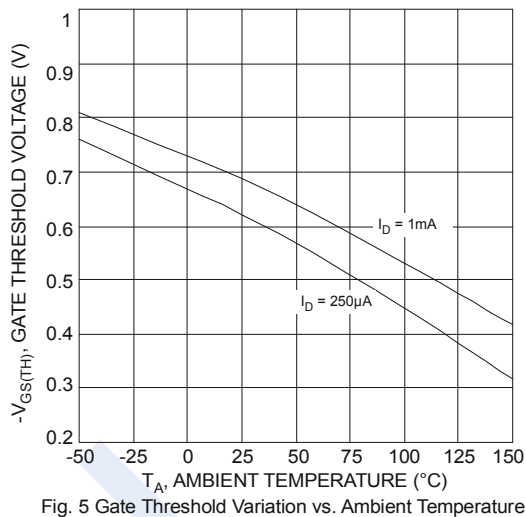
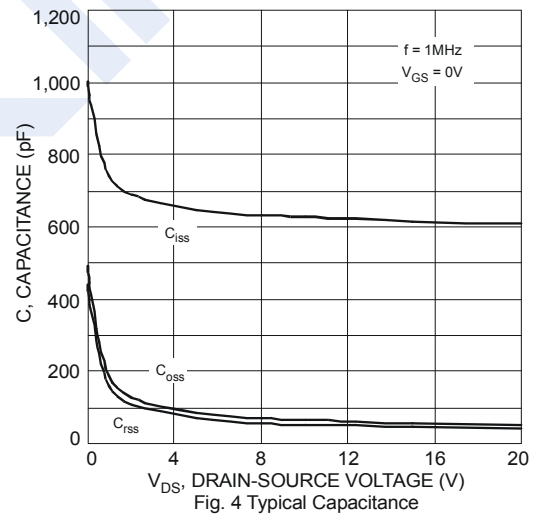
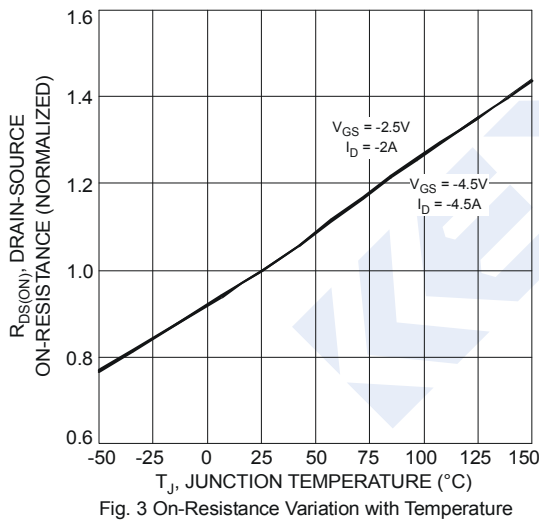
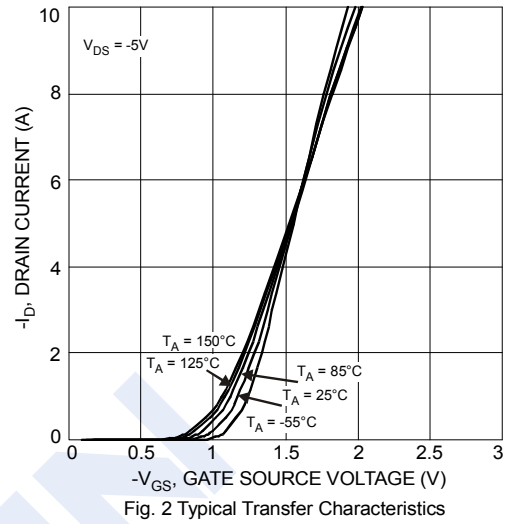
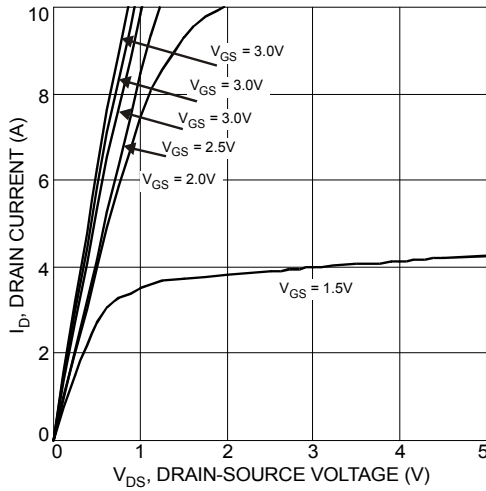
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250 μ A, V _{GS} =0V	-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-16V, V _{GS} =0V			-1	μ A
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±8V			±100	nA
		V _{DS} =0V, V _{GS} =±12V			±800	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250 μ A	-0.4		-0.9	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-1.5A			75	m Ω
		V _{GS} =-2.5V, I _D =-1.2A			96	
		V _{GS} =-1.8V, I _D =-1.2A			140	
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-1.5A		7		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-10V, f=1MHz		627		pF
Output Capacitance	C _{oss}			64		
Reverse Transfer Capacitance	C _{rss}			53		
Gate resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz		44.9		Ω
Total Gate Charge	Q _g	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-3A		6.5		nC
Gate Source Charge	Q _{gs}			0.9		
Gate Drain Charge	Q _{gd}			1.5		
Turn-On DelayTime	t _{d(on)}	V _{DS} = -10V, V _{GS} = -4.5V, R _L = 10Ω, R _G = 1Ω, I _D = -1A		12.5		ns
Turn-On Rise Time	t _r			10.3		
Turn-Off DelayTime	t _{d(off)}			46.5		
Turn-Off Fall Time	t _f			22.2		
Maximum Body-Diode Continuous Current	I _S				-1	A
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V			-1	V

■ Marking

Marking	DMF
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P-Channel MOSFET DMP1260 (KMP1260)

Typical Characteristics



P-Channel MOSFET DMP1260 (KMP1260)

■ Typical Characteristics

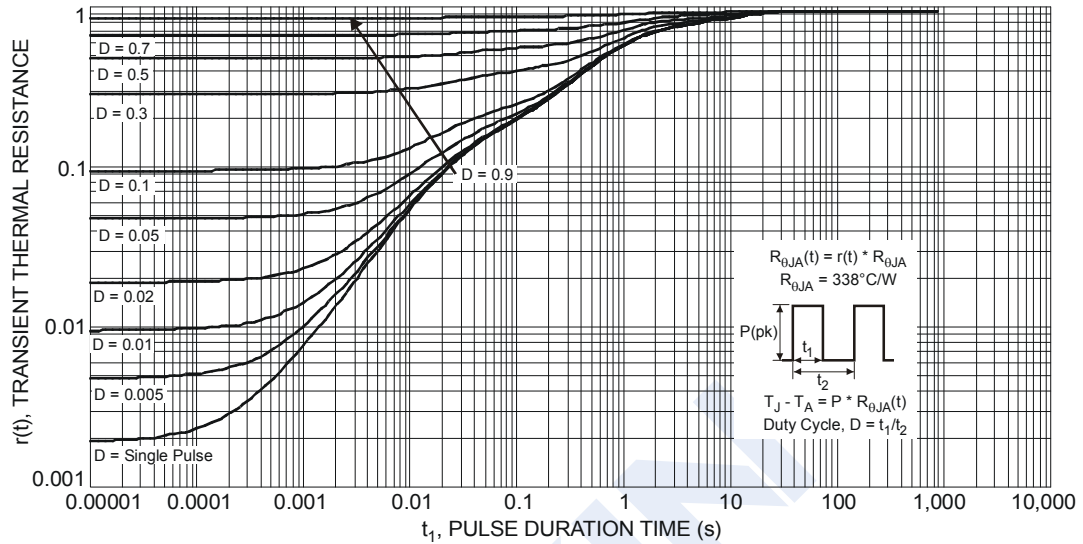


Fig. 7 Transient Thermal Response